DATA SHEET

NEC

SILICON POWER TRANSISTOR
2SC4814

NPN SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SC4814 is a power transistor featuring low-saturation voltage and high h_{FE}. This transistor is ideal for high-precision control such as PWM control for pulse motors or brushless motors in OA and FA equipment and for solenoid driving in automotive equipment.

In addition, this transistor features a package that can be auto-mounted in radial taping specifications, thus contributing to mounting cost reduction.

FEATURES

- Low $V_{CE(sat)}$: $V_{CE(sat)} \leq 0.3$ V @I_C = 1.5 A, I_B = 10 mA
- High h_{FE}: h_{FE} = 300 to 1,200 @V_{CE} = 2.0 V, I_C = 1.0 A
- On-chip dumper-diode
- Auto-mounting possible in radial taping specifications

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	V_{CBO}		120	V
Collector to emitter voltage	V_{CEO}		100	V
Emitter to base voltage	V_{EBO}		7.0	V
Collector current (DC)	$I_{C(DC)}$		±2.5	A
Collector current (pulse)	$I_{C(pulse)}$	PW ≤ 300 μs, duty cycle ≤ 10%	±5.0	A
Base current (DC)	$I_{B(DC)}$		1.0	A
Total power dissipation	P_T	Ta = 25°C	1.8	W
Junction temperature	T_j		150	°C
Storage temperature	T_{stg}		−55 to +150	°C

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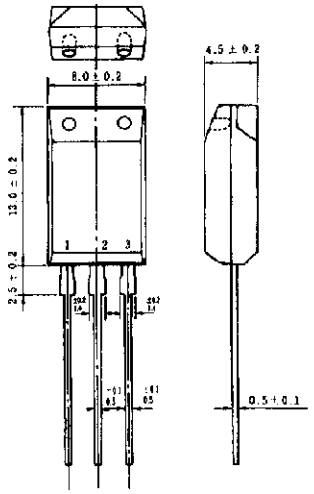
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 120 V, I_E = 0			50	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 5 V, I_C = 0			50	μA
DC current gain	h_{FE1}*	V_{CE} = 2 V, I_C = 1.0 A	300	700	1,200	–
DC current gain	h_{FE2}*	V_{CE} = 2 V, I_C = 1.5 A	250	600		–
Collector saturation voltage	$V_{CE(sat)}$*	I_C = 1.5 A, I_B = 10 mA			0.3	V
Base saturation voltage	$V_{BE(sat)}$*	I_C = 1.5 A, I_B = 10 mA			1.3	V
Gain bandwidth product	f_T	V_{CE} = 10 V, I_C = 1.0 A		60		MHz
Collector capacitance	C_{ob}	V_{CE} = 10 V, I_E = 0 , f = 1 MHz		40		pF
Turn-on time	t_{on}	I_C = 1.5 A, I_{B1} = –I_{B2} = 10 mA R_L = 8.0 Ω, V_{CC} = 12 V Refer to the test circuit.		0.5		μs
Storage time	t_{stg}			2.0		μs
Fall time	t_f			0.5		μs

* Pulse test PW ≤ 350 μs, duty cycle ≤ 2%

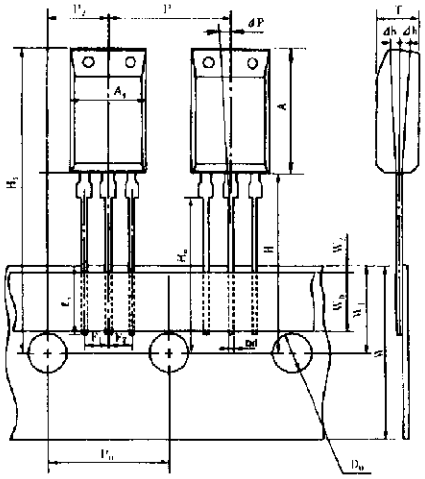
PACKAGE DRAWING (UNIT: mm)



Electrode Connection

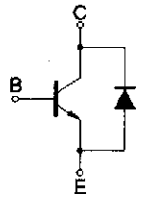
1. Base
2. Collector
3. Emitter

TAPING SPECIFICATION

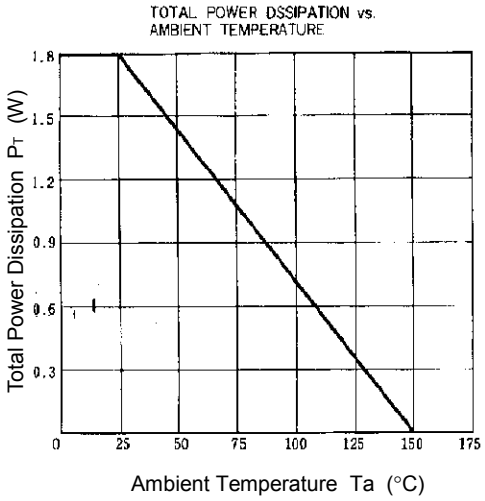


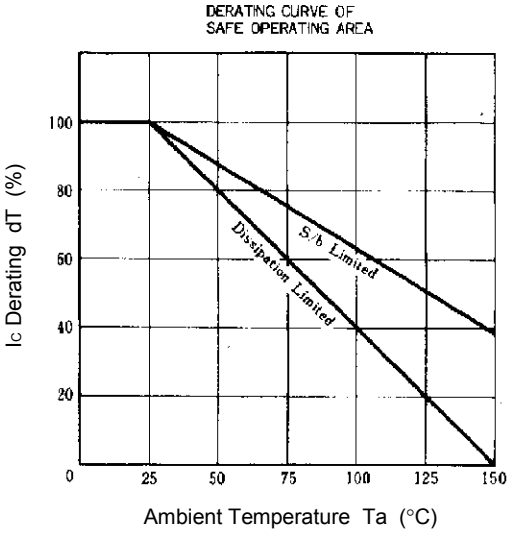
A_1	8.0±0.2
A	13.0±0.2
D_0	φ4.0±0.2
d	0.5±0.1
F_1	$2.5^{+0.4}_{-0.1}$
F_2	$2.5^{+0.4}_{-0.1}$
H	20.0 MAX.
H_0	16.0±0.5
H_1	32.2 MAX.
Δh	0±1.0
ℓ_1	2.5 MIN.
P	12.7±1.0
P_0	12.7±0.3
P_2	6.35±0.5
ΔP	0±1.3
T	4.5±0.2
W	$18.0^{+1.0}_{-0.5}$
W_0	5.0 MIN.
W_1	9.0±0.5
W_2	0.7 MAX.

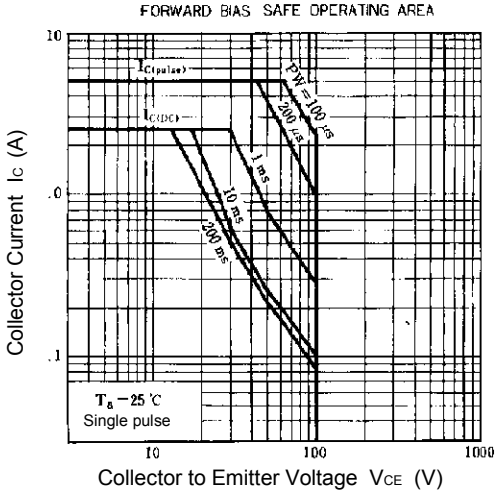
EQUIVALENT CIRCUIT

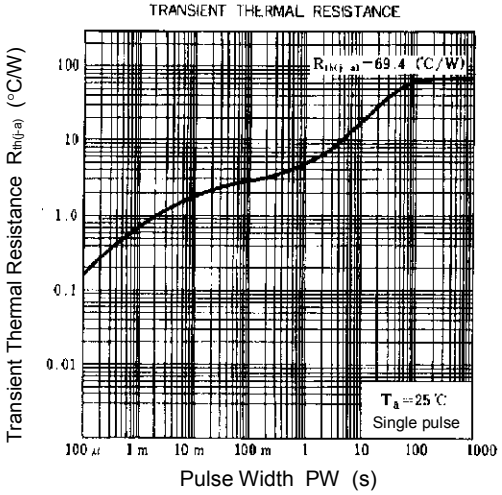


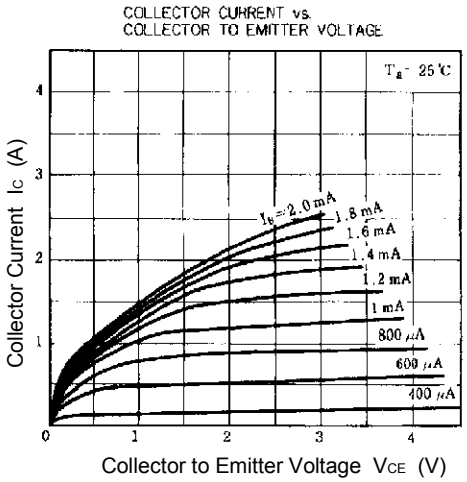
TYPICAL CHARACTERISTICS (Ta = 25°C)

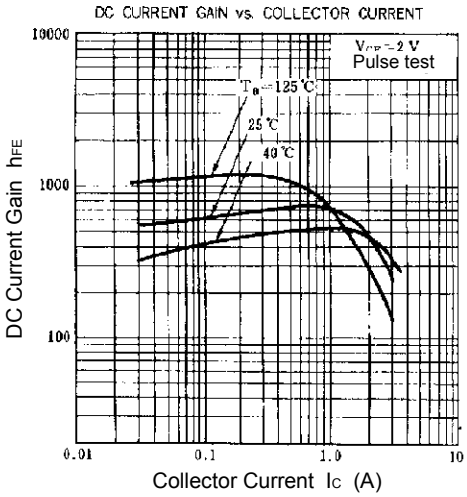




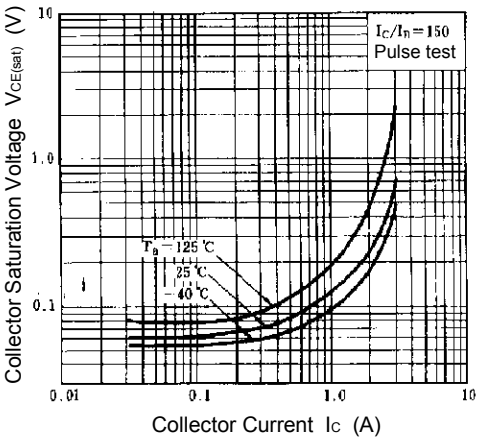




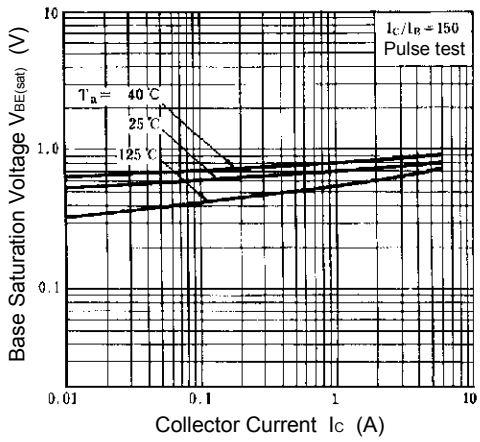




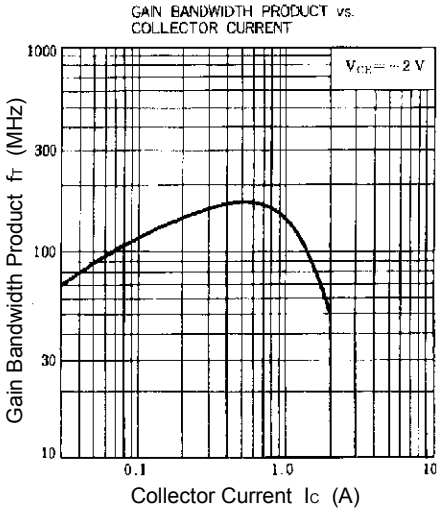
COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



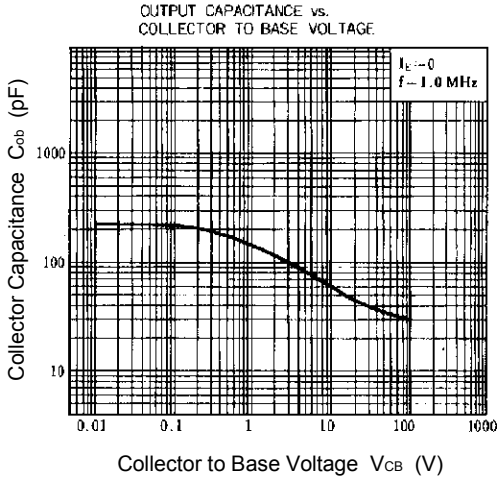
BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



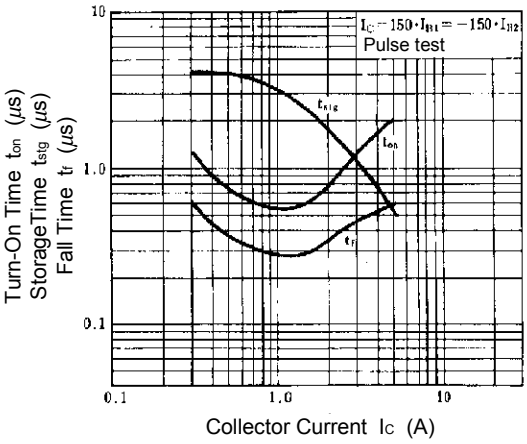
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



TURN ON TIME, STORAGE TIME AND FALL TIME vs. COLLECTOR CURRENT



SWITCHING TIME (t_{on}, t_{stg}, t_f) TEST CIRCUIT